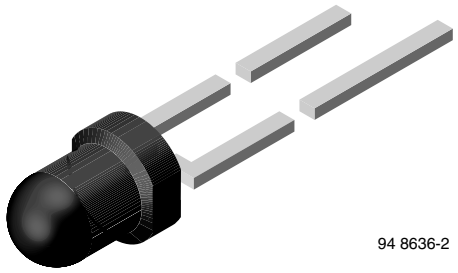
High Speed Infrared Emitting Diode, 940 nm, GaAlAs, MQW



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FEATURES

- Package type: leaded
- Package form: T-1, clear epoxy
- Dimensions: Ø 3 mm
- High speed
- High radiant power
- Low forward voltage
- Suitable for high pulse current operation
- Angle of half intensity: φ = ± 22°
- Peak wavelength: λ_p = 940 nm
- Good spectral matching to Si photodetectors
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb-free

e2

RoHS COMPLIANT

HALOGEN FREE GREEN (5-2008)

DESCRIPTION

VSLB4940 is a high speed infrared emitting diode in GaAlAs, MQW technology, molded in a clear plastic package.

APPLICATIONS

- Infrared remote control units
- Reflective sensors
- Light barriers

PRODUCT SUMMARY				
COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
VSLB4940	65	± 22	940	15

Note

- Test conditions see table “Basic Characteristics“

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VSLB4940	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	t_p/T = 0.1, t_p = 100 µs	I_{FM}	500	mA
Surge forward current	t_p = 100 µs	I_{FSM}	1	A
Power dissipation		P_V	160	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	-25 to +85	°C
Storage temperature range		T_{stg}	-40 to +100	°C
Soldering temperature	t ≤ 5 s, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction / ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	300	K/W

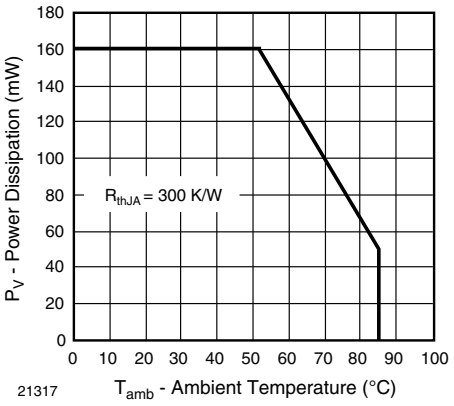


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

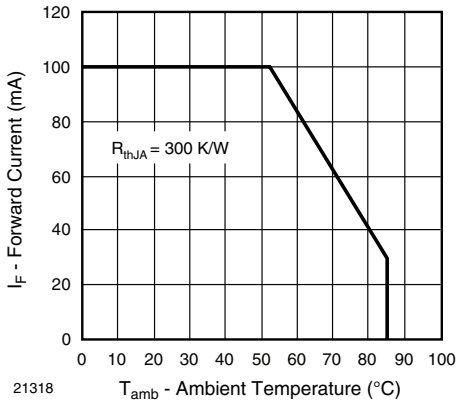


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)						
PARAMETER	**TEST CONDITION**	**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Forward voltage	I_F = 100 mA, t_p = 20 ms	V_F	1.22	1.42	1.62	V
Temperature coefficient of V_F	I_F = 1 mA	TK_{VF}	-	-1.5	-	mV/K
Reverse current	V_R = 5 V	I_R	-	-	10	µA
Junction capacitance	V_R = 0 V, f = 1 MHz, E = 0 mW/cm²	C_J	-	21	-	pF
Radiant intensity	I_F = 100 mA, t_p = 20 ms	I_e	32	65	110	mW/sr
Radiant power	I_F = 100 mA, t_p = 20 ms	ϕe	-	40	-	mW
Temperature coefficient of radiant power	I_F = 1 mA	$TK\phi_e$	-	-1.1	-	%/K
	I_F = 100 mA	$TK\phi_e$	-	-0.51	-	%/K
Angle of half intensity		φ	-	± 22	-	deg
Peak wavelength	I_F = 30 mA	λ_p	-	940	-	nm
Spectral bandwidth	I_F = 30 mA	$\Delta\lambda$	-	30	-	nm
Temperature coefficient of I_p	I_F = 30 mA	$TK_{\lambda p}$	-	0.25	-	nm
Rise time	I_F = 100 mA, 20 % to 80 %	t_r	-	15	-	ns
Fall time	I_F = 100 mA, 20 % to 80 %	t_f	-	15	-	ns
Virtual source diameter		d	-	2	-	mm

BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

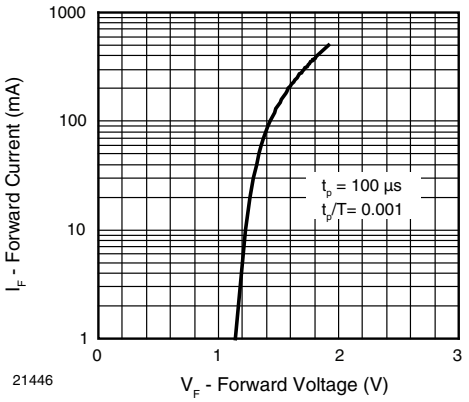


Fig. 3 - Forward Current vs. Forward Voltage

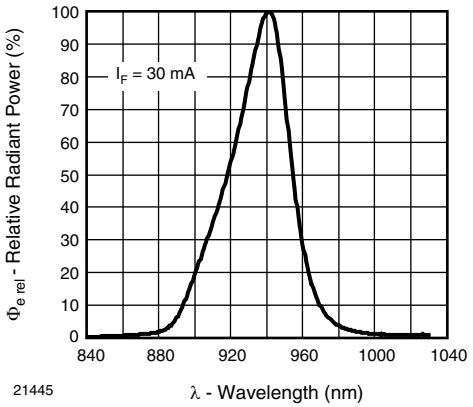


Fig. 6 - Relative Radiant Power vs. Wavelength

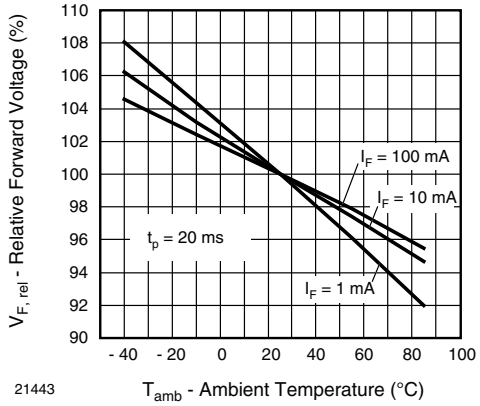


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

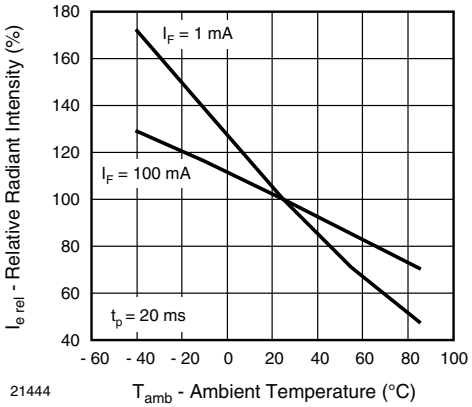


Fig. 7 - Relative Radiant Intensity vs. Ambient Temperature

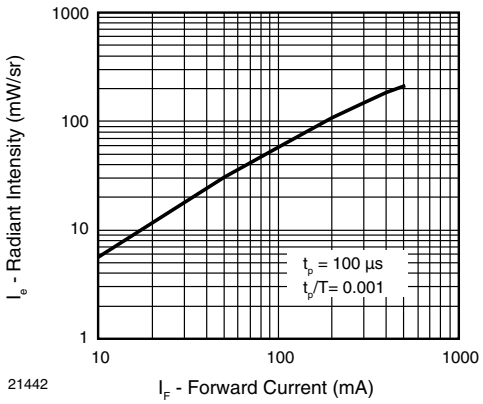


Fig. 5 - Radiant Intensity vs. Forward Current

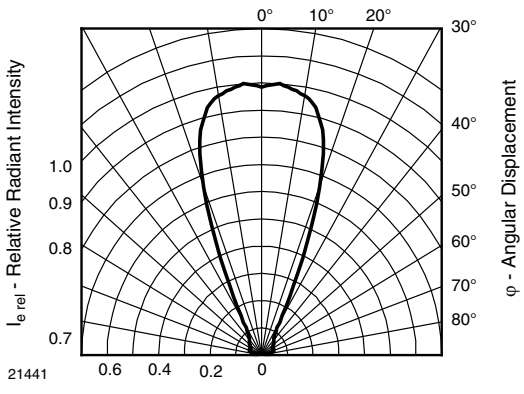
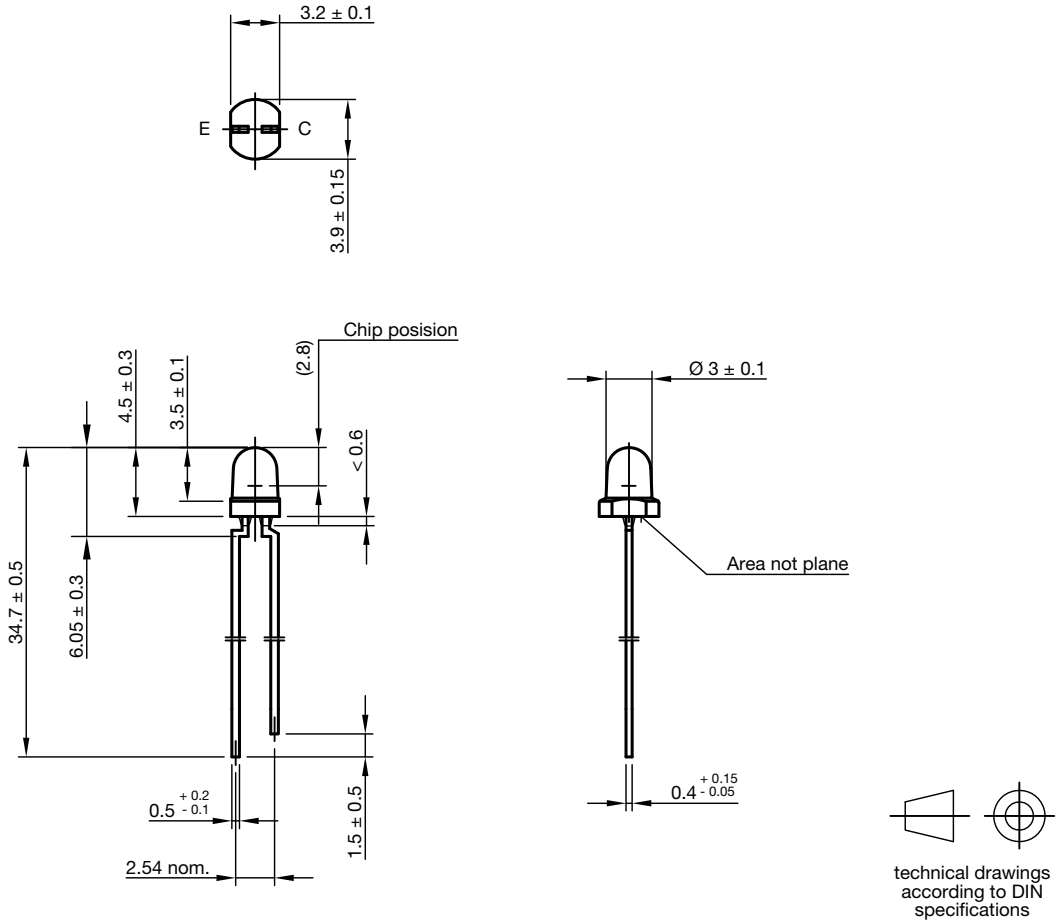


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



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